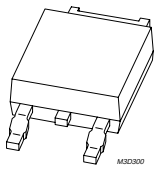


BUK92150-55A

TrenchMOS™ logic level FET

Rev. 03 — 30 May 2002 **Product data**

1. Description

N-channel enhancement mode field-effect power transistor in a plastic package using TrenchMOS™ technology, featuring very low on-state resistance.

Product availability:

BUK92150-55A in SOT428 (D-PAK).

2. Features

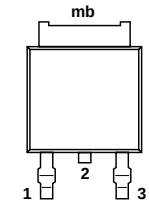
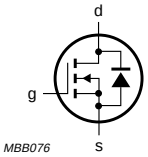
- TrenchMOS™ technology
- Q101 compliant
- 175 °C rated
- Logic level compatible.

3. Applications

- Automotive and general purpose power switching:
  - 12 V and 24 V loads
  - Motors, lamps and solenoids.

4. Pinning information

Table 1: Pinning - SOT428 (D-PAK), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)		
2	drain (d)		
3	source (s)		
mb	mounting base; connected to drain (d)		

SOT428 (D-PAK)

5. Quick reference data

Table 2: Quick reference data

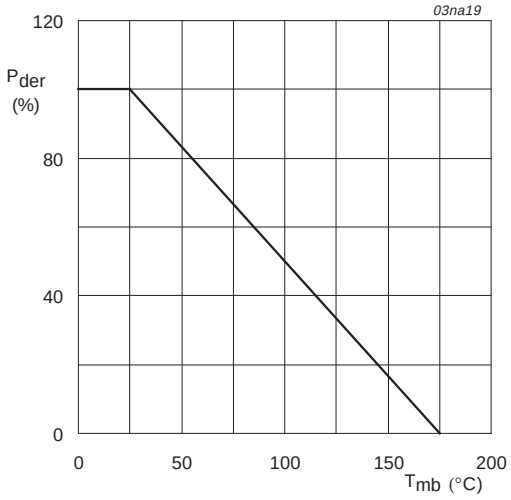
Symbol	Parameter	Conditions	Typ	Max	Unit
V_{DS}	drain-source voltage (DC)		-	55	V
I_D	drain current (DC)	T_{mb} = 25 °C; V_{GS} = 5 V	-	11	A
P_{tot}	total power dissipation	T_{mb} = 25 °C	-	36	W
T_j	junction temperature		-	175	°C
R_{DSon}	drain-source on-state resistance	T_j = 25 °C; V_{GS} = 5 V; I_D = 5 A	120	140	mΩ
		T_j = 25 °C; V_{GS} = 4.5 V; I_D = 5 A	-	155	mΩ
		T_j = 25 °C; V_{GS} = 10 V; I_D = 5 A	97	125	mΩ
		T_j = 175 °C; V_{GS} = 5 V; I_D = 5 A	-	280	mΩ

6. Limiting values

Table 3: Limiting values

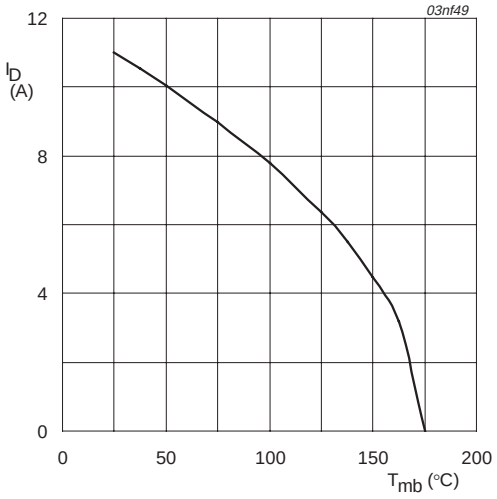
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	55	V
V_{DGR}	drain-gate voltage (DC)	R_{GS} = 20 kΩ	-	55	V
V_{GS}	gate-source voltage (DC)		-	±15	V
I_D	drain current (DC)	T_{mb} = 25 °C; V_{GS} = 5 V; Figure 2 and 3	-	11	A
		T_{mb} = 100 °C; V_{GS} = 5 V; Figure 2	-	7.8	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs; Figure 3	-	44	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Figure 1	-	36	W
T_{stg}	storage temperature		–55	+175	°C
T_j	junction temperature		–55	+175	°C
Source-drain diode					
I_{DR}	reverse drain current (DC)	T_{mb} = 25 °C	-	11	A
I_{DRM}	peak reverse drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs	-	44	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; I_D = 11 A; $V_{DS} \leq 55$ V; V_{GS} = 5 V; R_{GS} = 50 Ω; starting T_j = 25 °C	-	16	mJ



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

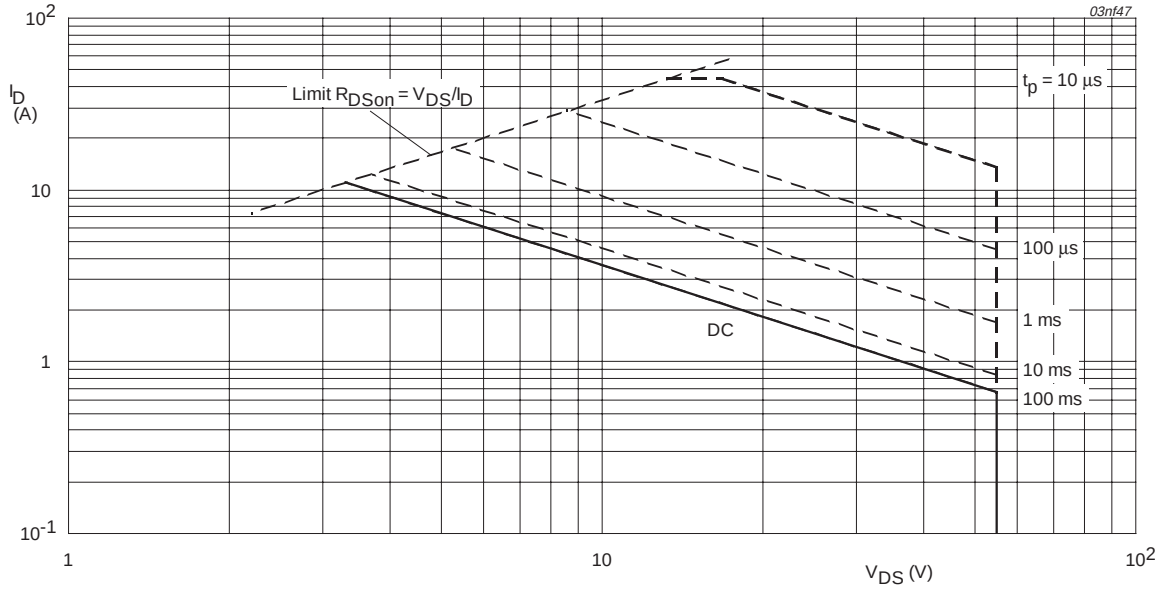
Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$V_{GS} \geq 4.5$ V

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Continuous drain current as a function of mounting base temperature.



T_{mb} = 25 °C; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

7. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	71.4	-	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	4.1	K/W

7.1 Transient thermal impedance

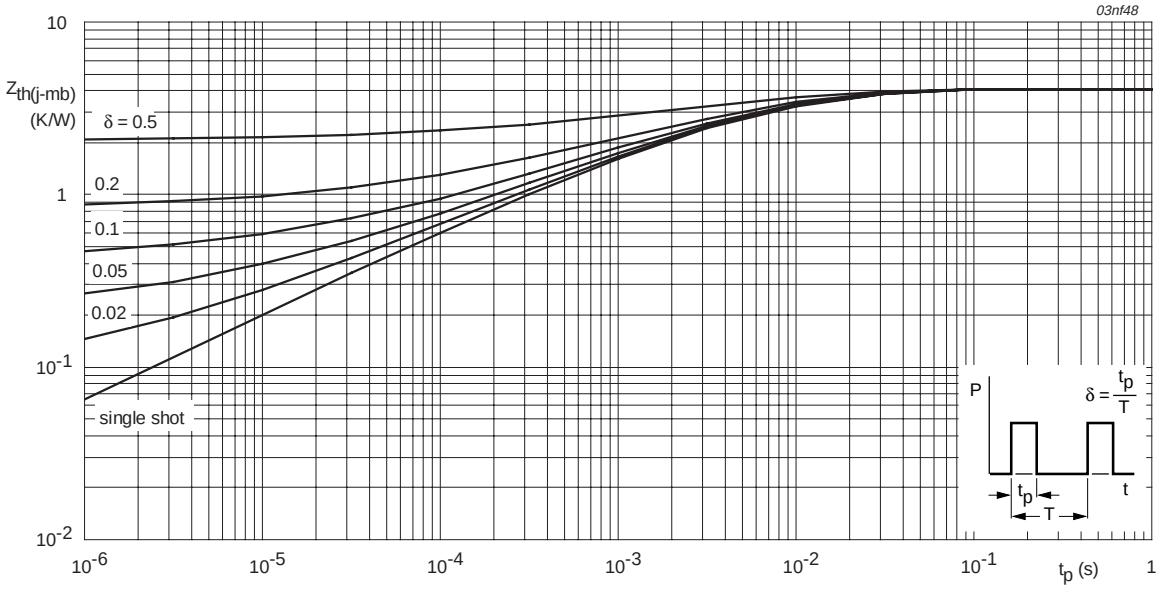


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

8. Characteristics

Table 5: Characteristics

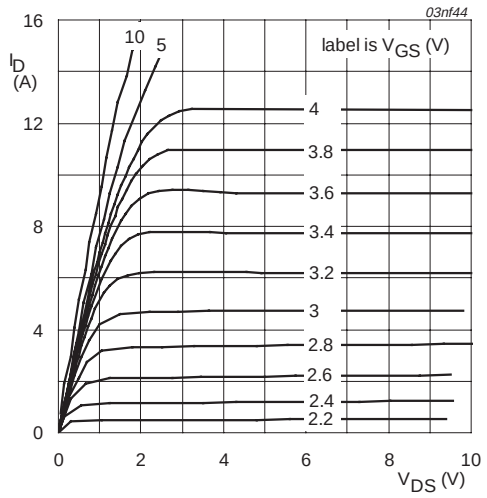
T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V				
		T_j = 25 °C	55	-	-	V
		T_j = –55 °C	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; Figure 9				
		T_j = 25 °C	1	1.5	2	V
		T_j = 175 °C	0.5	-	-	V
		T_j = –55 °C	-	-	2.3	V
I_{DSS}	drain-source leakage current	V_{DS} = 55 V; V_{GS} = 0 V				
		T_j = 25 °C	-	0.05	10	μA
		T_j = 175 °C	-	-	500	μA
I_{GSS}	gate-source leakage current	V_{GS} = ±10 V; V_{DS} = 0 V	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; Figure 7 and 8				
		T_j = 25 °C	-	120	140	mΩ
		T_j = 175 °C	-	-	280	mΩ
		V_{GS} = 4.5 V; I_D = 5 A;	-	-	155	mΩ
		V_{GS} = 10 V; I_D = 5 A;	-	97	125	mΩ
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	V_{GS} = 5 V; V_{DD} = 44 V; I_D = 5 A; Figure 14	-	6	-	nC
Q_{gs}	gate-to-source charge		-	0.72	-	nC
Q_{gd}	gate-to-drain (Miller) charge		-	2.6	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; Figure 12	-	240	338	pF
C_{oss}	output capacitance		-	50	65	pF
C_{rss}	reverse transfer capacitance		-	40	58	pF
$t_{d(on)}$	turn-on delay time	V_{DD} = 20 V; R_L = 3.3 Ω; V_{GS} = 5 V; R_G = 10 Ω;	-	8	-	ns
t_r	rise time		-	57	-	ns
$t_{d(off)}$	turn-off delay time		-	16	-	ns
t_f	fall time		-	13	-	ns
L_d	internal drain inductance	measured from drain to centre of die	-	2.5	-	nH
L_s	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH

Table 5: Characteristics...*continued*

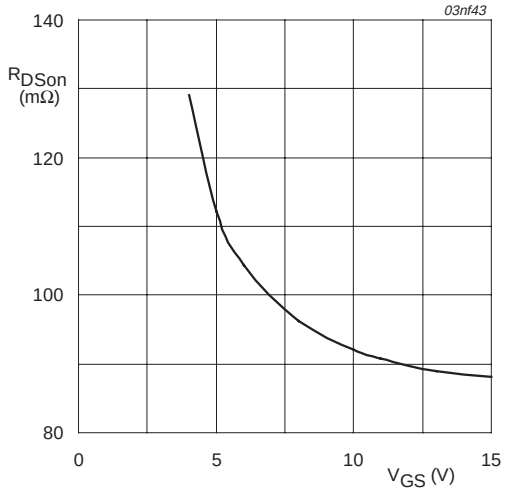
T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	I_S = 15 A; V_{GS} = 0 V; Figure 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = −100 A/µs V_{GS} = −10 V; V_{DS} = 30 V	-	24	-	ns
Q_r	recovered charge		-	26	-	nC



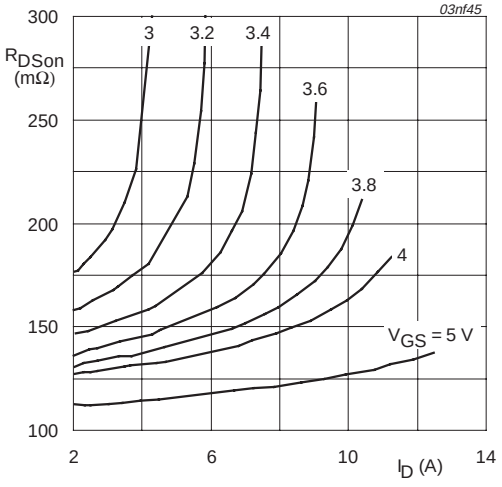
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



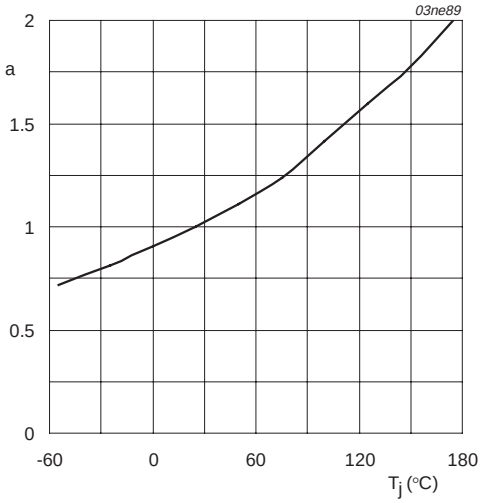
T_j = 25 °C; I_D = 5 A

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.



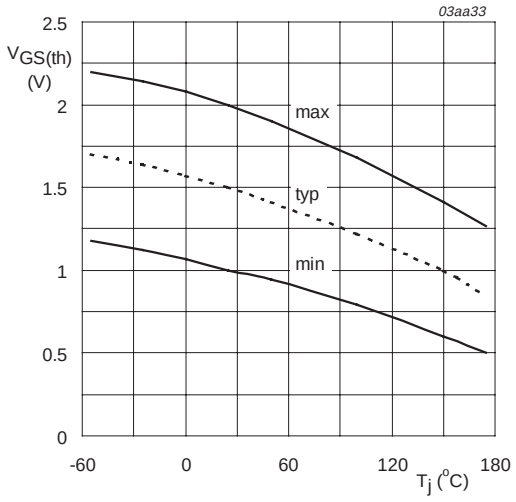
T_j = 25 °C

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



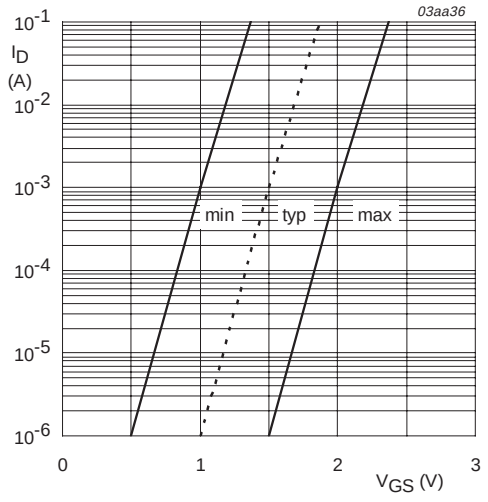
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



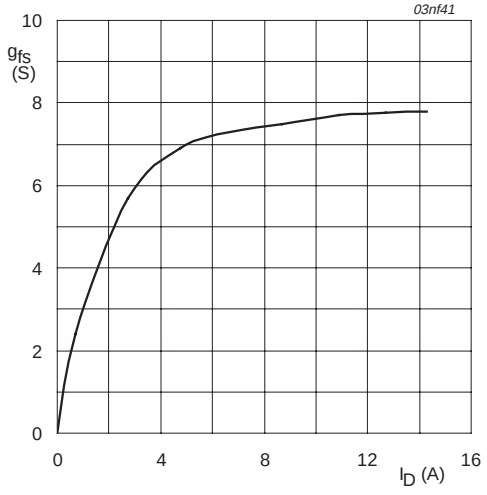
I_D = 1 mA; V_{DS} = V_{GS}

Fig 9. Gate-source threshold voltage as a function of junction temperature.



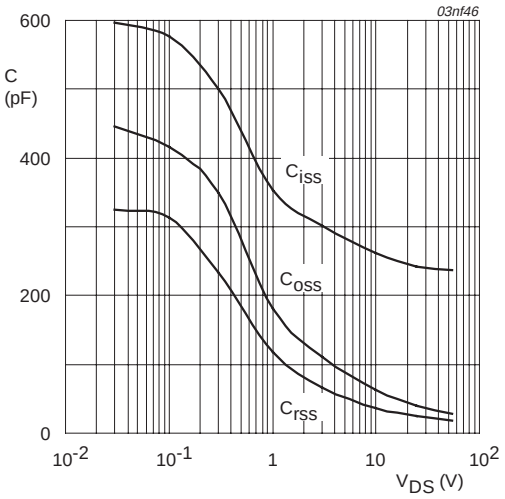
T_j = 25 °C; V_{DS} = V_{GS}

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



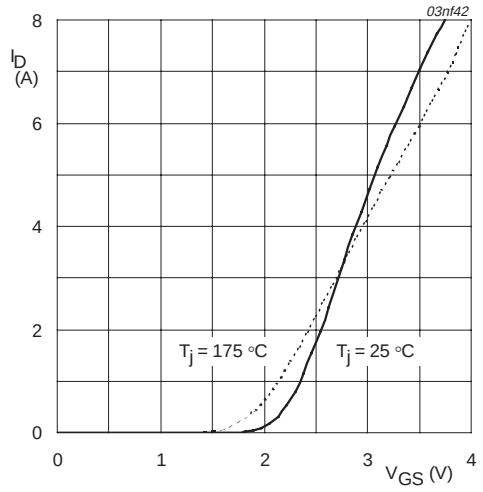
T_j = 25 °C; V_{DS} = 25 V

Fig 11. Forward transconductance as a function of drain current; typical values.



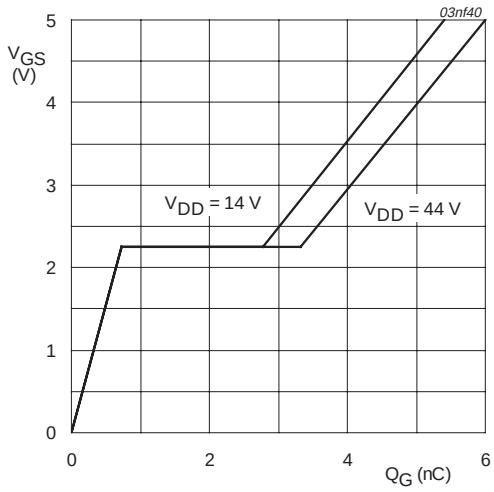
V_{GS} = 0 V; f = 1 MHz

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



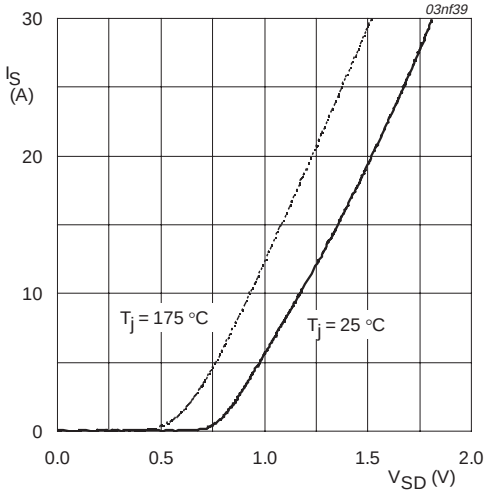
V_{DS} = 25 V

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



T_j = 25 °C; I_D = 5 A

Fig 14. Gate-source voltage as a function of turn-on gate charge; typical values.



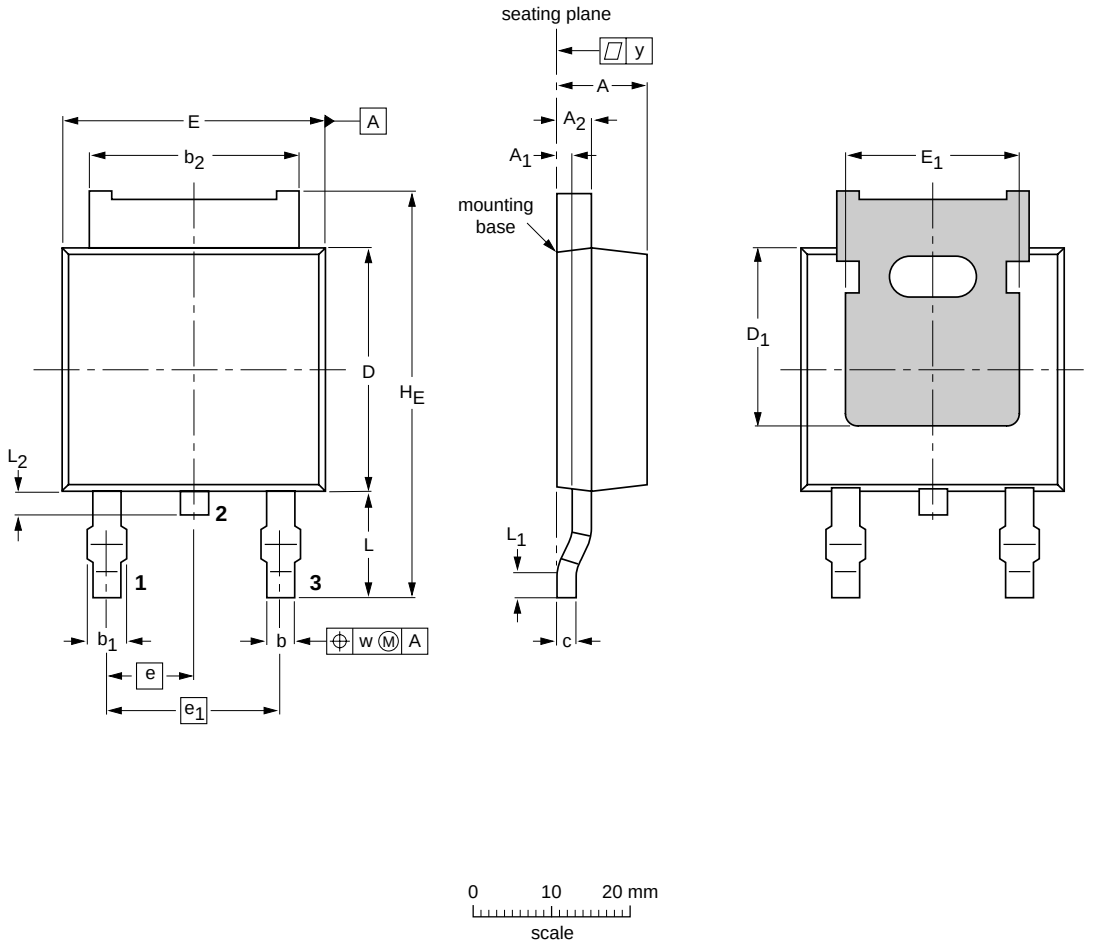
V_{GS} = 0 V

Fig 15. Reverse diode current as a function of reverse diode voltage; typical values.

9. Package outline

Plastic single-ended surface mounted package (Philips version of D-PAK); 3 leads (one lead cropped)

SOT428



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 (1)	A_2	b	b_1	b_2	c	D	D_1 min.	E	E_1	e	e_1	H_E	L	L_1 min.	L_2	w	y max.
mm	2.38 2.22	0.65 0.45	0.93 0.73	0.89 0.71	1.1 0.9	5.46 5.26	0.4 0.2	6.22 5.98	4.0	6.73 6.47	4.81 4.45	2.285	4.57	10.4 9.6	2.95 2.55	0.5	0.9 0.5	0.2	0.2

Note

1. Measured from heatsink back to lead.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT428		TO-252	SC-63			~~99-09-13~~ 01-12-11

Fig 16. SOT428 (D-PAK).

10. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
03	20020530	-	**Product data (9397 750 09725)** Modifications: • R_{DSon} Max @ 5 V lowered to 140 mΩ. Values @ 10 V and 4.5 V adjusted accordingly.
02	20010703	-	**Product data; second version.**
01	20000690	-	**Product data; initial manuscript version.**

11. Data sheet status

Data sheet status[1]	Product status[2]	Definition
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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9397 750 09725

Contents

Date of release: 30 May 2002 **Document order number: 9397 750 09725**